

ABSTRACT

A nitride semiconductor device according to the present invention includes a p-type nitride semiconductor layer, an
5 n-type nitride semiconductor layer, and an active layer interposed between the p-type nitride semiconductor layer and the n-type nitride semiconductor layer. The p-type nitride semiconductor layer includes: a first p-type nitride semiconductor layer containing Al and Mg; and a second p-type
10 nitride semiconductor layer containing Mg. The first p-type nitride semiconductor layer is located between the active layer and the second p-type nitride semiconductor layer, and the second p-type nitride semiconductor layer has a greater band gap than a band gap of the first p-type nitride
15 semiconductor layer.